

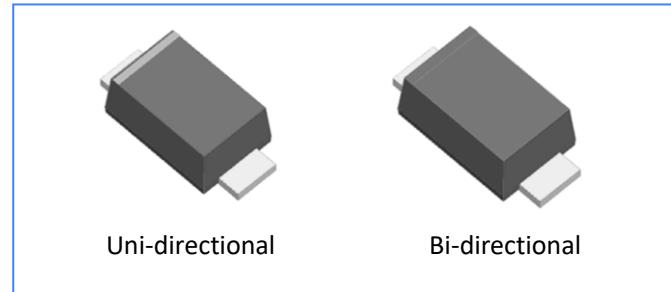
## SMF Series

### Description

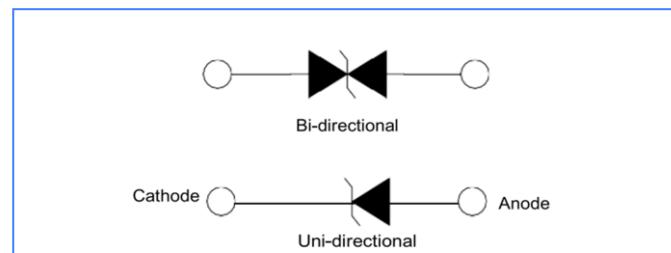
The SMF series is designed specifically to protect sensitive electronic equipment from voltage transients induced by lightning and other transient voltage events. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. The SMF series is supplied in YINT Semiconductor's exclusive, cost-effective, highly reliable and is ideally suited for use in communication systems, automotive, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer Applications.

### Features

- Case: SOD123FL
- Excellent clamping capability
- 200 W peak pulse power capability with a 10/1000  $\mu$ s waveform
- Typical failure mode is a short circuit condition for current events exceeding component rating
- Fast response time: typically less than 1.0ps from 0 Volts to VB min.
- IEC61000-4-2 (ESD)  $\pm 30kV$  (air),  $\pm 30kV$  (contact).



### Functional Diagram



### Applications

TVS devices are ideal for the transient voltage clamp protection of I/O Interfaces, DC power line bus and other circuits used in Telecom, Computer, Industrial and Consumer electronic applications.

### Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Pulse Power Dissipation at $T_A=25^\circ C$ by 10/1000 $\mu$ s Waveform	$P_{PK}$	200	W
Peak Forward Surge Current, 8.3ms Single Half Sine Wave <sup>1</sup>	$I_{FSM}$	20	A
Maximum Instantaneous Forward Voltage at 50A for Unidirectional Only	$V_F$	3.5	V
Operating Temperature Range	$T_J$	-55 to +150	°C
Storage Temperature Range	$T_{STG}$	-55 to +150	°C

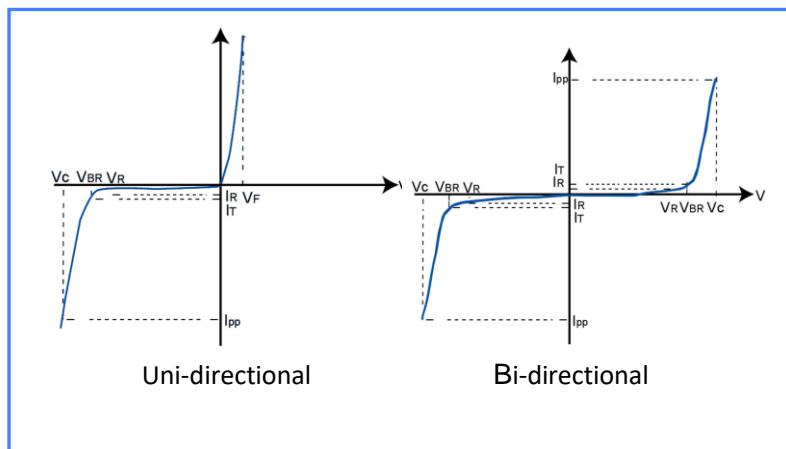
NOTES:

1. Measured on 8.3ms single half sine wave or equivalent square wave for unidirectional device only, duty cycle=4 per minute maximum.

### Electrical characteristics ( $T_A = 25^\circ C$ unless otherwise noted)

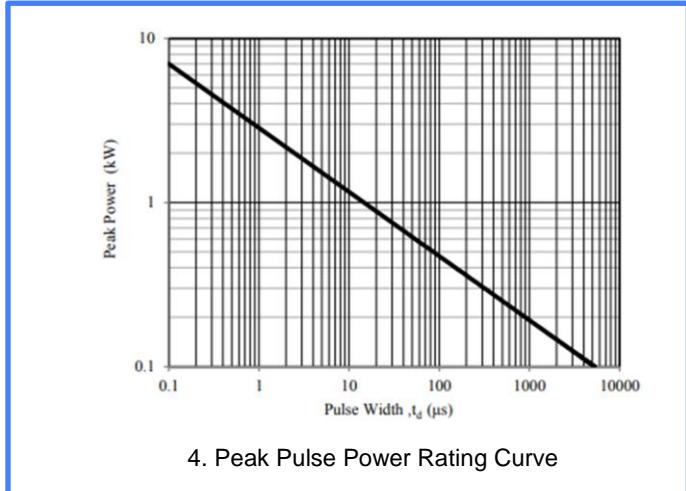
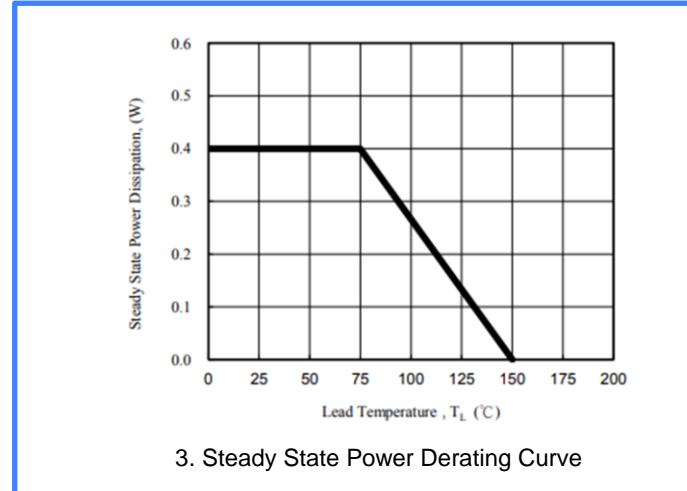
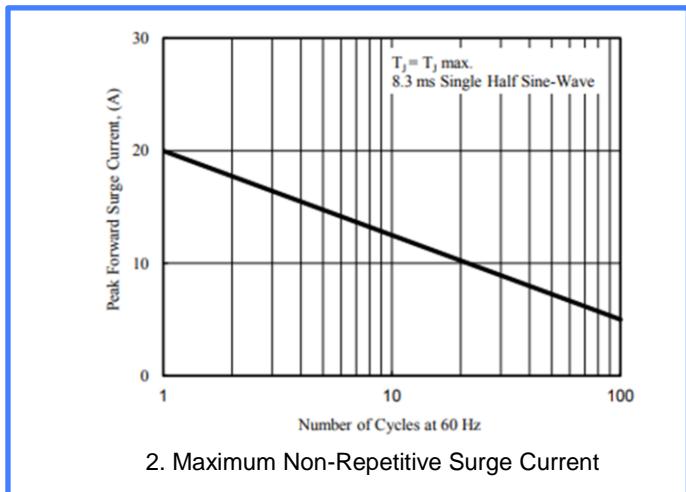
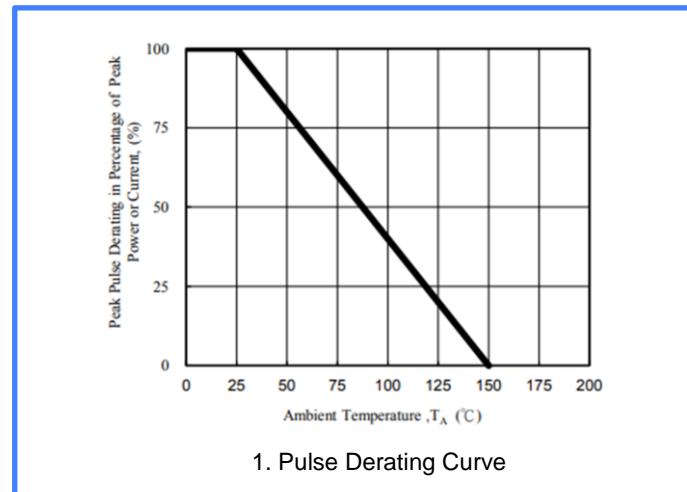
Part Number (Bi)	Part Number (Uni)	MARKING		Reverse Stand off Voltage $V_R$ (Volts)	Breakdown Voltage $V_{BR}$ (Volts)@ $I_T$		Test Current $I_T$ (mA)	Maximum Reverse Leakage $I_R$ @ $V_R$ ( $\mu$ A)	Maximum Peak Pulse Current $I_{PP}$ (A)	Maximum Clamping Voltage $V_C$ @ $I_{PP}$ (V)
		BI	UNI		Min .V	Max .V				
SMF3.3CA	SMF3.3A	3.3C	3.3A	3.3	4.1	6.5	10	150	27.40	8.0

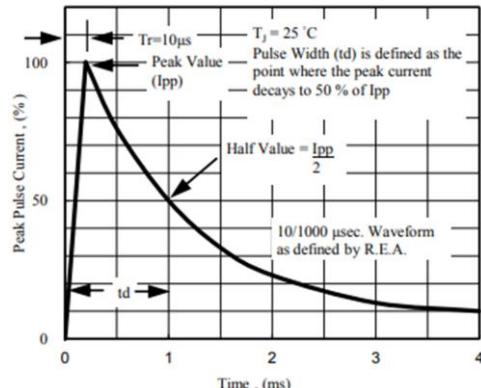
## I-V Curve characteristics



Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$ (Test Current)

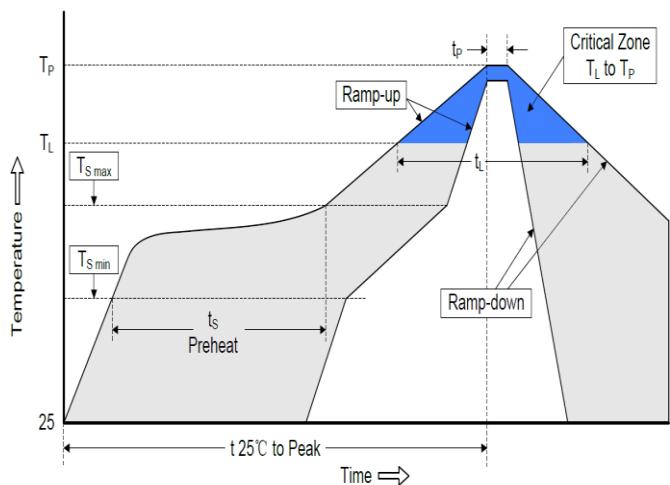
## Rating & Characteristic Curves





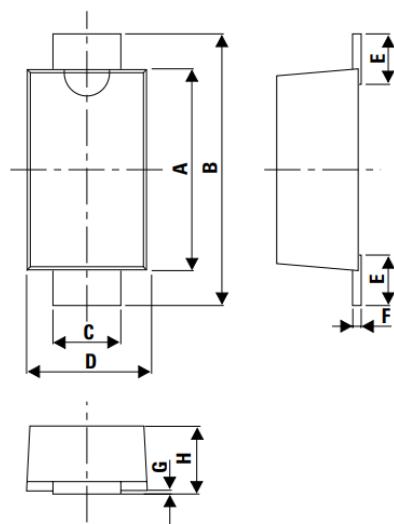
5. Pulse Waveform

## Soldering parameters



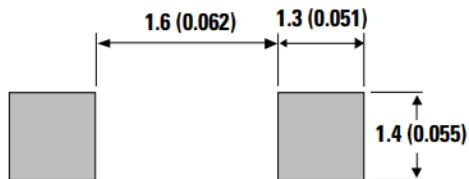
Profile Feature	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_P$ )	3°C/second max.
Preheat	<ul style="list-style-type: none"> <li>-Temperature Min (<math>T_{S \min}</math>)</li> <li>-Temperature Max (<math>T_{S \max}</math>)</li> <li>-Time (min to max)(<math>t_S</math>)</li> </ul>
$T_{S \max}$ to $T_L$	<ul style="list-style-type: none"> <li>-Ramp-up Rate</li> </ul>
Time maintained above:	<ul style="list-style-type: none"> <li>- Temperature (<math>T_L</math>)</li> <li>- Time (<math>t_L</math>)</li> </ul>
Peak Temperature ( $T_P$ )	260°C
Time within 5°C of actual Peak Temperature ( $t_P$ )	20-40 seconds
Ramp-down Rate	6°C /second max.
Time 25°C to Peak Temperature	8 minutes max.

## Package outline dimensions in millimeters



Dimensions	Millimeter	
	Min	Max
A	2.50	3.10
B	3.40	3.90
C	0.70	1.20
D	1.50	2.00
E	0.35	0.90
F	0.05	0.26
G	0.00	0.10
H	0.90	1.25

## Mounting Pad Layout



## Disclaimer

Specifications are subject to change without notice.

The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.

Users should verify actual device performance in their specific applications.